Silicon NPN Power Transistors 2SC1569

DESCRIPTION

·With TO-220 package
·High breakdown voltage
·High transition frequency

APPLICATIONS

·For color TV chroma output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

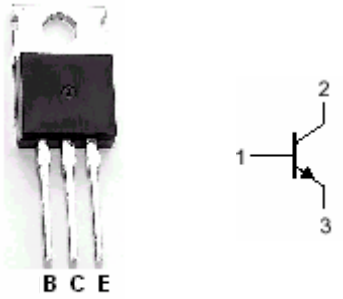

Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings (Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		0.2	A
P_C	Collector power dissipation	T_a=25□	1.5	W
		T_C=25□	12.5	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=10μA ;I_E=0	300			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=1mA ;I_B=0	300			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=10μA ;I_C=0	7			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=100mA ;I_B=20mA			1.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=100mA ;I_B=20mA			1.2	V
I_{CBO}	Collector cut-off current	V_{CB}=100V;I_E=0			1.0	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			1.0	μA
h_{FE}	DC current gain	I_C=50mA ; V_{CE}=10V	40		170	
C_{OB}	Output capacitance	I_E=0; V_{CB}=10V;f=1MHz		65		pF
f_T	Transition frequency	I_C=30mA ; V_{CE}=10V	40			MHz

PACKAGE OUTLINE

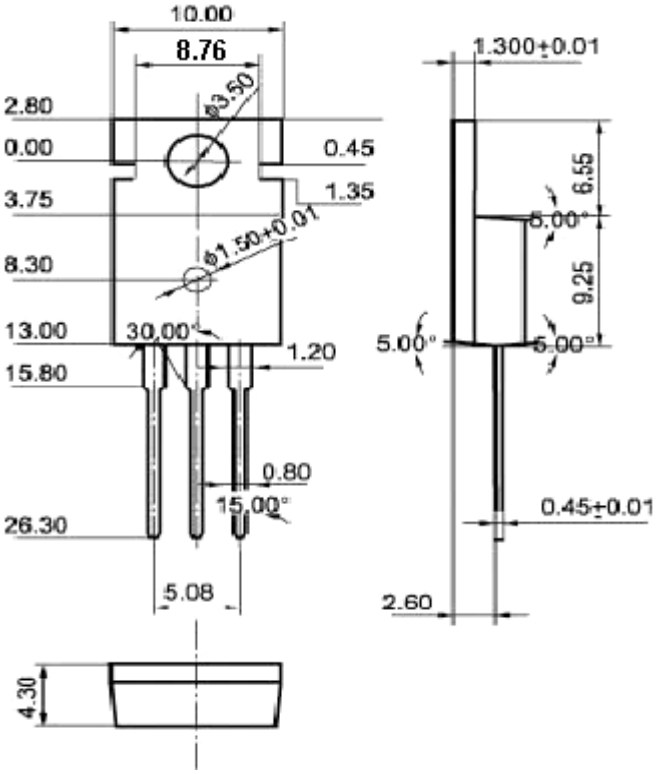

Fig.2 outline dimensions (unindicated tolerance:±0.10 mm)